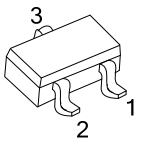
2N7002K **Preliminary** ***Power MOSFET***

300m Amps, 60 Volts N-CHANNEL ENHANCEMENT MODE MOSFET



SOT-23-3
(JEDEC TO-236)

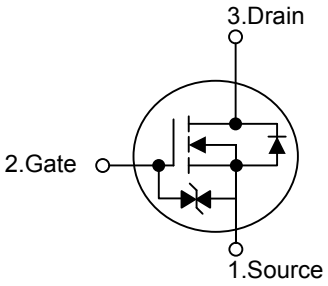
■ DESCRIPTION

The UTC **2N7002K** uses advanced technology to provide excellent $R_{DS(ON)}$, low gate charge and low gate voltages during operation. This device is suitable for use as a load switch or in PWM applications.

■ FEATURES

* Low Reverse Transfer Capacitance (C_{RSS} = typical 3.0 pF)
* ESD Protected
* Fast Switching Capability
* Avalanche Energy Specified
* Improved dv/dt Capability, High Ruggedness

■ SYMBOL

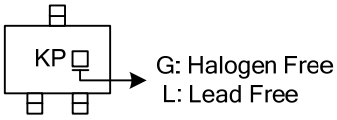


■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment						Packing
Lead Free	Halogen Free		1	2	3	4	5	6	
2N7002KL-AE2-R	2N7002KG-AE2-R	SOT-23-3	S	G	D	-	-	-	Tape Reel

2N7002KG-AE2-R (1)Packing Type (2)Package Type (3)Halogen Free	(1) R: Tape Reel (2) AE2: SOT-23-3 (3) G: Halogen Free, L: Lead Free

■ MARKING



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■ ABSOLUTE MAXIMUM RATINGS (T_a = 25°C)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	60	V
Gate-Source Voltage		V_{GSS}	±20	V
Drain Current	Continuous	I_D	300	mA
	Pulse(Note 2)		800	
Power Dissipation		P_D	350	mW
Derating above T_A=25°C			2.8	mW/°C
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (T_a=25°C)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=10μA	60			V
Drain-Source Leakage Current	I_{DSS}	V_{DS}=60V, V_{GS}=0V			1.0	μA
Gate-Source Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS}=±20V			±10	μA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	V_{DS}=10V, I_D=1mA	1.0	1.85	2.5	V
Static Drain-Source On-Resistance (Note)	$R_{DS(ON)}$	V_{GS}=10V, I_D=0.5A			2	Ω
		V_{GS}=4.5V, I_D=200mA			4	
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	V_{DS}=25V, V_{GS}=0V, f=1.0MHz		25	50	pF
Output Capacitance	C_{OSS}			10	25	pF
Reverse Transfer Capacitance	C_{RSS}			3.0	5.0	pF
SWITCHING PARAMETERS						
Turn-ON Delay Time	$t_{D(ON)}$	I_D=0.2 A, V_{DD}=30V, V_{GS}=10V,		12	20	ns
Turn-OFF Delay Time	$t_{D(OFF)}$	R_L=150Ω, R_G=10Ω		20	30	ns
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Drain-Source Diode Forward Voltage	V_{SD}	V_{GS}=0V, Is=115mA (Note)		0.88	1.5	V
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				0.8	A
Maximum Continuous Drain-Source Diode Forward Current	Is				115	mA

Note: 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch. Minimum land pad size.
2. Pulse width≦300μs, Duty cycle≦1%

■ TEST CIRCUITS AND WAVEFORMS

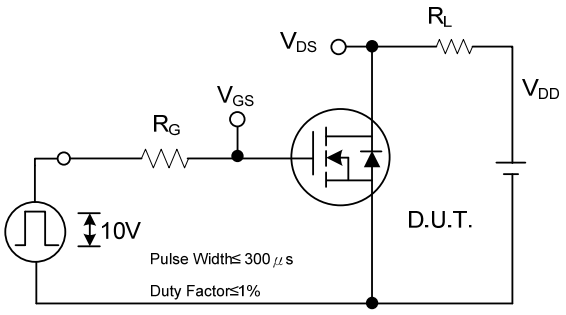

Fig. 2A Switching Test Circuit

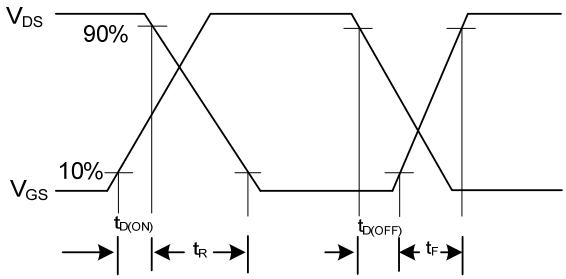

Fig. 2B Switching Waveforms

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